TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

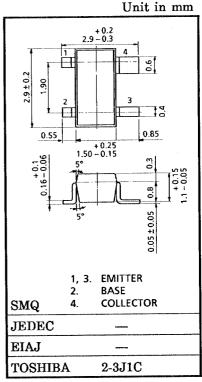
MT4S07

VHF~UHF Band Low Noise Amplifier Applications

- Low Noise Figure: NF = 1.5dB  $(V_{CE} = 3 V, I_C = 5 mA, f = 2 GHz)$
- High Gain: |S21e|<sup>2</sup> = 9.5dB (VCE = 3 V, IC = 15 mA, f = 2 GHz)

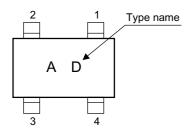
### Maximum Ratings ( $Ta = 25^{\circ}C$ )

項目	記号	定格	単位	
Collector-base voltage	V <sub>CBO</sub>	10	V	
Collector-emitter voltage	V <sub>CEO</sub>	5	V	
Emitter-base voltage	V <sub>EBO</sub>	1.5	V	
Collector current	Ι <sub>C</sub>	25	mA	
Base current	Ι <sub>Β</sub>	10	mA	
Collector power dissipation	PC	150	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	Tstg	-55~125	°C	



Weight : 0.012 g

### Marking



000707EAA1

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# Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f <sub>T</sub>	$V_{CE} = 3 V, I_{C} = 10 mA$	10	12	_	GHz
Insertion gain	S21e  <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	8	_	dB
	S21e  <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 15 \text{ mA}, \text{ f} = 2 \text{ GHz}$	7.5	10.5	_	
Noise figure	NF(1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$	_	1.6	3	dB
	NF(2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		1.5	3	

## **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 V, I_{E} = 0$	_	_	0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 1 V, I_{C} = 0$	_	_	1	μA
DC current gain	h <sub>FE</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	70	_	140	—
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB}=1 \ V, \ I_{E}=0, \ f=1 \ MHz  (Note)$	—	0.4	0.85	pF

Note:  $C_{re}\xspace$  is measured by 3 terminal method with capacitance bridge.

## Caution

This device electrostatic sensitivity. Please handle with caution